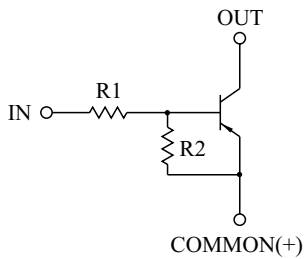


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

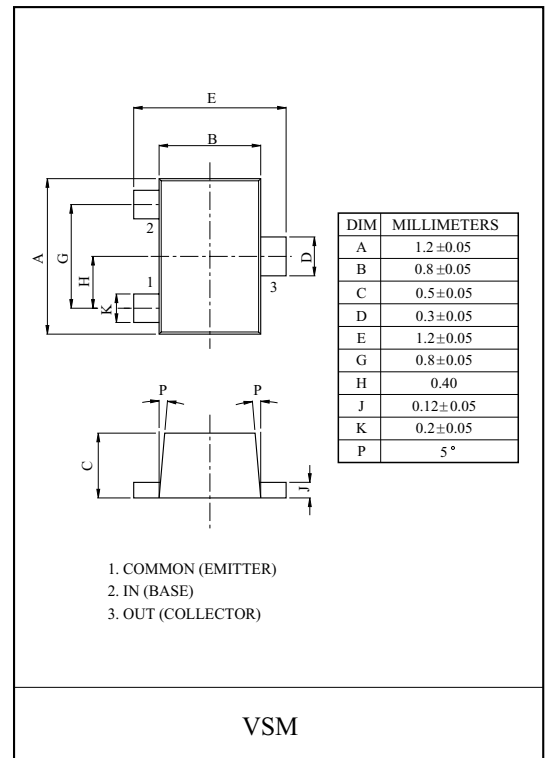
- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.
- High Packing Density.

EQUIVALENT CIRCUIT

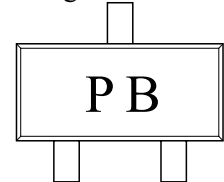


BIAS RESISTOR VALUES

TYPE NO.	R1(k)	R2(k)
KRA302VS	10	10



Marking



MAXIMUM RATING (Ta=25)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Output Voltage	V _O	-50	V
Input Voltage	V _I	-30, 10	V
Output Current	I _O	-100	mA
Power Dissipation	P _D	100	mW
Junction Temperature	T _j	150	
Storage Temperature Range	T _{stg}	-55 150	

KRA302VS

ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Cut-off Current		$I_{O(OFF)}$	$V_O=-50V, V_I=0$	-	-	-500	nA
DC Current Gain		G_I	$V_O=-5V, I_O=-10mA$	50	80	-	
Output Voltage		$V_{O(ON)}$	$I_O=-10mA, I_I=-0.5mA$	-	-0.1	-0.3	V
Input Voltage (ON)		$V_{I(ON)}$	$V_O=-0.2V, I_O=-5mA$	-	-1.8	-2.4	V
Input Voltage (OFF)		$V_{I(OFF)}$	$V_O=-5V, I_O=-0.1mA$	-1.0	-1.2	-	V
Transition Frequency		f_T^*	$V_O=-10V, I_O=-5mA$	-	200	-	MHz
Input Current		I_I	$V_I=-5V$	-	-	-0.88	mA
Input Resistor		R1	-	7	10	13	k
Resistor Ratio		R2/R1	-	0.8	1.0	1.2	
Switching Time	Rise Time	t_r	$V_O=-5V$	-	0.06	-	μs
	Storage Time	t_{stg}	$V_{IN}=-5V$	-	1.1	-	
	Fall Time	t_f	$R_L=1k$	-	0.24	-	

Note : * Characteristic of Transistor Only.

KRA302VS

